PATENT ASSIGNMENT

Electronic Version v1.1 Stylesheet Version v1.1

SUBMISSION TYPE: NEW ASSIGNMENT

NATURE OF CONVEYANCE: ASSIGNMENT

CONVEYING PARTY DATA

Name	Execution Date
Group IV Semiconductor, Inc.	01/21/2013

RECEIVING PARTY DATA

Name:	Kirsteen Mgmt. Group LLC		
Street Address:	711 Centerville Road, Suite 400		
City:	Wilmington		
State/Country:	DELAWARE		
Postal Code:	19808		

PROPERTY NUMBERS Total: 24

Property Type	Number
Patent Number:	7923925
Patent Number:	7616272
Patent Number:	7839467
Patent Number:	7081664
Patent Number:	7122842
Patent Number:	7679102
Patent Number:	8093604
Patent Number:	7800117
Patent Number:	7888686
Patent Number:	8089080
Patent Number:	8198638
Patent Number:	7923288
Patent Number:	8232611
Application Number:	60989227
Application Number:	61084686
	PATENT

Application Number:	60441413
Application Number:	60500686
Application Number:	60754185
Application Number:	60786730
Application Number:	60800422
Application Number:	61083751
Application Number:	60884266
Application Number:	60971373
Application Number:	61187424

CORRESPONDENCE DATA

Fax Number: 2062240779

Correspondence will be sent via US Mail when the fax attempt is unsuccessful.

Phone: (206)682-8100

Email: efiling@cojk.com

Correspondent Name: Kevan L. Morgan, Esq.

Address Line 1: Christensen O'Connor Johnson Kindness

Address Line 2: 1420 Fifth Avenue, Suite 2800
Address Line 4: Seattle, WASHINGTON 98101-2347

ATTORNEY DOCKET NUMBER:	5-51672
NAME OF SUBMITTER:	Kevan L. Morgan

Total Attachments: 11

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ASSIGNMENT OF PATENT RIGHTS

For good and valuable consideration, the receipt of which is hereby acknowledged, Group IV Semiconductor, Inc., an Ontario corporation, with an office at 400 March Road, Ottawa, Canada K2K 3H4 ("Assignor"), does hereby sell, assign, transfer, and convey unto Kirsteen Mgmt. Group LLC, a Delaware limited liability company, with an address at 2711 Centerville Rd, Suite 400, Wilmington, DE 19808 ("Assignee"), or its designees, all right, title, and interest that exist today and may exist in the future in and to any and all of the following (collectively, the "Patent Rights"):

(a) the provisional patent applications, patent applications and patents listed in the table below (the "*Patents*");

			Title of Patent and First Named
Patent or Application No.	Country	Filing Date	<u>Inventor</u>
7923925	US	11/19/2008	Light emitting device with a
			stopper layer structure
			Thomas Macelwee
7616272	US	08/17/2007	Electroluminescent films for
			backlighting liquid crystal
			displays
			Carla Miner
7839467	US	10/16/2009	Color tuneable
			electroluminescent devices
	1		Carla Miner
7081664	US	01/22/2004	Doped semiconductor powder
			and preparation thereof
			E G. Hill
7122042	110	07/22/2004	E. Steven Hill
7122842	US	07/22/2004	Solid state white light emitter and
			display using same
			E. Steven Hill
7679102	US	12/21/2006	Carbon passivation in solid-state
7679102	US	12/21/2006	light emitters
			ingit enitters
			George Chik
8093604	US	12/21/2006	Engineered structure for solid-
0035001		12/21/2000	state light emitters
			state right emitters
			George Chik
7800117	US	12/21/2006	Pixel structure for a solid state
			light emitting device

Patent or Application No.	olid-
CNZL200680050141.8 CN 12/22/2006 Pixel structure for a solid light emitting device George Chik CNZL200680050151.1 CN 12/22/2006 Engineered structure for s state light emitters George Chik KR10-2008-7018271 KR 12/22/2006 Pixel structure for a solid light emitting device George Chik KR10-2008-7018286 KR 12/22/2006 Engineered structure for s state light emitters George Chik IN01337/2008 IN 12/22/2006 Engineered structure for s state light emitters George Chik Engineered structure for s state light emitters George Chik Engineered structure for s state light emitters George Chik George Chik IN01337/2008 IN 12/22/2006 Engineered structure for s state light emitters George Chik	olid-
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7888686 US 01/16/2008 Pixel structure for a solid	state
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8089080 US 07/23/2009 Engineered structure for h	nigh.
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8198638 US 07/14/2010 Light emitting device stru	
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Thomas Macelwee	
7923288 US 09/10/2008 Zinc oxide thin film	
electroluminescent device	
Jaan Davil Maal	S
8232611 US 06/14/2010 Jean-Paul Noel High Quality Gate Dielect	S
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Method of Formation The	tric For

			Title of Patent and First Named
Patent or Application No.	Country	Filing Date	<u>Inventor</u>
			Carla Miner

- (b) all patents and patent applications (i) to which any of the Patents directly or indirectly claims priority, and/or (ii) for which any of the Patents directly or indirectly forms a basis for priority;
- (c) all reissues, reexaminations, extensions, continuations, continuations in part, continuing prosecution applications, requests for continuing examinations, divisions, registrations of any item in any of the foregoing categories (a) and (b);
- (d) all foreign patents, patent applications, and counterparts relating to any item in any of the foregoing categories (a) through (c), including, without limitation, certificates of invention, utility models, industrial design protection, design patent protection, and other governmental grants or issuances;
- (e) all items in any of the foregoing in categories (b) through (d), whether or not expressly listed as Patents below and whether or not claims in any of the foregoing have been rejected, withdrawn, cancelled, or the like;
- (f) inventions, invention disclosures, and discoveries described in any of the Patents and/or any item in the foregoing categories (b) through (e) that (i) are included in any claim in the Patents and/or any item in the foregoing categories (b) through (e), (ii) are subject matter capable of being reduced to a patent claim in a reissue or reexamination proceeding brought on any of the Patents and/or any item in the foregoing categories (b) through (e), and/or (iii) could have been included as a claim in any of the Patents and/or any item in the foregoing categories (b) through (e);
- (g) all rights to apply in any or all countries of the world for patents, certificates of invention, utility models, industrial design protections, design patent protections, or other governmental grants or issuances of any type related to any item in any of the foregoing categories (a) through (f), including, without limitation, under the Paris Convention for the Protection of Industrial Property, the International Patent Cooperation Treaty, or any other convention, treaty, agreement, or understanding;
- (h) all causes of action (whether known or unknown or whether currently pending, filed, or otherwise) and other enforcement rights under, or on account of, any of the Patents and/or any item in any of the foregoing categories (b) through (g), including, without limitation, all causes of action and other enforcement rights for

- (1) damages,
- (2) injunctive relief, and
- (3) any other remedies of any kind

for past, current, and future infringement; and

(i) all rights to collect royalties and other payments under or on account of any of the Patents and/or any item in any of the foregoing categories (b) through (h).

For greater certainty, notwithstanding any other provision in this assignment, the Patents do not include any of Seller's inventions that were first conceived after July 30, 2010.

Assignor hereby authorizes the respective patent office or governmental agency in each jurisdiction to issue any and all patents, certificates of invention, utility models or other governmental grants or issuances that may be granted upon any of the Patent Rights in the name of Assignee, as the assignee to the entire interest therein.

Assignor will, at the reasonable request of Assignee, do all things necessary, proper, or advisable, including without limitation, the execution, acknowledgment, and recordation of specific assignments, oaths, declarations, and other documents on a country-by-country basis, to assist Assignee in obtaining, perfecting, sustaining, and/or enforcing the Patent Rights.

The terms and conditions of this Assignment of Patent Rights will inure to the benefit of Assignee, its successors, assigns, and other legal representatives and will be binding upon Assignor, its successors, assigns, and other legal representatives.

IN W	TINESS WH	EREOF th	is Assignment of Pa	tent Rights is ex	recuted at ಿಗ ಿಯ ೪
on _	Jan	2)	, 2013.		

ASSIGNOR:

Group IV Semiconductor, Inc.

(Signature MUST be attested)

ATTESTATION OF SIGNATURE PURSUANT TO 28 U.S.C. § 1746

Page 4

The undersigned witnessed the signature of Hen NAR to the above Assignment of Patent Rights on behalf of Group IV Semiconductor, Inc. and makes the following statements:

- 1. I am over the age of 18 and competent to testify as to the facts in this Attestation block if called upon to do so.
- 2. Shen NAC is personally known to me (or proved to me on the basis of satisfactory evidence) and appeared before me on Thu zill 3 2013 to execute the above Assignment of Patent Rights on behalf of Group IV Semiconductor, Inc.
- 3. Stephen NAOF subscribed to the above Assignment of Patent Rights on behalf of Group IV Semiconductor, Inc.

I declare under penalty of perjury under the laws of the United States of America that the statements made in the three (3) numbered paragraphs immediately above are true and correct.

EXECUTED on <u>Jawon</u> 021, 2013

Lisa <u>Reckanp</u>

Print Name: <u>Lisa Bechanp</u>

ASSIGNMENT OF RIGHTS IN CERTAIN ASSETS

For good and valuable consideration, the receipt of which is hereby acknowledged, Group IV Semiconductor, Inc., an Ontario corporation, with an office at 400 March Road, Ottawa, Canada K2K 3H4 ("Assignor"), does hereby sell, assign, transfer, and convey unto Kirsteen Mgmt. Group LLC, a Delaware limited liability company, with an address at 2711 Centerville Rd, Suite 400, Wilmington, DE 19808 ("Assignee"), or its designees, the right, title, and interest in and to any and all of the following provisional patent applications, patent applications, patents, and other governmental grants or issuances of any kind (the "Certain Assets"):

			Title of Patent and First Named
Patent or Application No.	Country	Filing Date	Inventor
60/989227	US	11/20/2007	Electroluminescent device with a stopper layer
			Thomas Macelwee
61/084686	US	07/30/2008	Buffer layer for electrodes in light emitting devices Jean-Paul Noel
PCT/CA2008/002034	WO	11/20/2008	
PC1/CA2008/002034	WO	11/20/2008	A light emitting device with a stopper layer structure Thomas Macelwee
PCT/CA2008/001481	WO	08/15/2008	Electroluminescent films for backlighting liquid crystal displays Carla Miner
TW097131371	TW	08/15/2008	Electroluminescent films for backlighting liquid crystal displays Carla Miner
60/441413	US	01/22/2003	Preparation of type IV semiconductor nanocrystals doped with rare-earth ions and product thereof E. Steven Hill
60/441485	US	01/22/2003	Applications of IV semiconductor nanocrystals doped with rareearth ions E. Steven Hill
60/450661	US	03/03/2003	Applications of IV semiconductor nanocrystals doped with rareearth ions E. Steven Hill
CA2513574	CA	01/22/2004	Doped semiconductor nanocrystal layers, doped semiconductor powders and

Patent or Application No.	Country	Filing Date	Title of Patent and First Named Inventor
			photonic devices employing such layers or powders
			E. Steven Hill
CN200480002694.7	CN	01/22/2004	Unable to verify
			Unable to verify
EP04704158.7	EP	01/22/2004	Rare earth doped group IV nanocrystal layers
			E. Steven Hill
10/761338	US	01/22/2004	Broadband optical pump source for optical amplifiers, planar optical amplifiers, planar optical circuits and planar optical lasers fabricated using group IV semiconductor nanocrystals
10/7/1400	TIC	01/22/2004	E. Steven Hill
10/761408	US	01/22/2004	Light emitting diodes and planar optical lasers using IV semiconductor nanocrystals
			E. Steven Hill
10/761409	US	01/22/2004	Doped semiconductor nanocrystal layers and preparation thereof
			E. Steven Hill
IN03203/2005	IN	01/22/2004	Doped semiconductor nanocrystal layers, doped semiconductor powers and photonic devices employing such layers or powers E. Steven Hill
JP2006-500439	JP	01/22/2004	Doped semiconductor nanocrystal layers, doped semiconductor powers and photonic devices employing such layers or powers E. Steven Hill
KR10-2005-7013325	KR	01/22/2004	Doped semiconductor
MATO-2003-7013323	IXIX	01/22/2007	nanocrystal layers, doped semiconductor powders and photonic devices employing such layers or powders E. Steven Hill
PCT/CA2004/000075	WO	01/22/2004	Doped semiconductor
			nanocrystal layers and

			Title of Patent and First Named
Patent or Application No.	Country	Filing Date	Inventor
			preparation thereof
			F 6. 1171
DCT/C A 200 A (00007)	WO	01/22/2004	E. Steven Hill
PCT/CA2004/000076	WO	01/22/2004	Rare earth doped group IV
			nanocrystal layers
			E. Steven Hill
11/533036	US	09/19/2006	Doped semiconductor
11/222020		05/15/2000	nanocrystal layers and
			preparation thereof
			E. Steven Hill
60/500686	US	09/08/2003	Solid state white light emitter and
			display using same
			7.0
ED04727092 0	ED	07/22/2004	E. Steven Hill
EP04737983.9	EP	07/22/2004	Solid state white light emitter and
			display using same
			E. Steven Hill
CN200480025794.1	CN	07/22/2004	Solid state white light emitter and
		***************************************	display using same
			E. Steven Hill
CA2538276	CA	07/22/2004	Solid state white light emitter and
			display using same
PCT/C 4 2004/001050	WO	07/22/2004	E. Steven Hill
PCT/CA2004/001059	WO	07/22/2004	Solid state white light emitter and display using same
			display using same
			E. Steven Hill
IN00960/2006	IN	07/22/2004	Solid state white light emitter and
			display using same
			E. Steven Hill
KR10-2006-7004616	KR	07/22/2004	Solid state white light emitter and
			display using same
			E Stavan Hill
JP2006-525011	JP	07/22/2004	E. Steven Hill Solid state white light emitter and
J1 2000-323011	31	0772272004	display using same
			aisping using sume
			E. Steven Hill
60/754185	US	12/28/2005	Semiconductor lighting
			George Chik
60/786730	US	03/29/2006	Composite layered film structure
			for light emitting devices
			Caaraa Chiil
			George Chik

Patent or Application No.	Country	Filing Date	<u>Title of Patent and First Named</u> Inventor
60/800422	US	05/16/2006	Carbon doping as a means to passivate silicon nanocrystals in SRSO-SiO2 engineered film structure for light emitting devices
			George Chik
CA2635303	CA	12/22/2006	Engineered structure for solid- state light emitters
			George Chik
CA2635307	CA	12/22/2006	Pixel structure for a solid state light emitting device
			George Chik
EP06840558.8	EP	12/22/2006	Engineered structure for solid- state light emitters
			George Chik
EP06840559.6	EP	12/22/2006	Pixel structure for a solid state light emitting device
			ingint cirritating device
			George Chik
JP2008-547815	JP	12/22/2006	Engineered structure for solid- state light emitters
			George Chik
PCT/CA2006/002132	WO	12/22/2006	Engineered structure for solid- state light emitters
			George Chik
PCT/CA2006/002133	WO	12/22/2006	Pixel structure for a solid state light emitting device
			George Chik
61/083751	US	07/25/2008	Solid-state light emitters using rare earths and aluminum
			Iain Calder
60/884266	US	01/10/2007	Light emitting devices with ZnO or a ZnO alloy thin film structure
			E. Steven Hill
60/971373	US	09/11/2007	Zinc oxide thin film
			electroluminescent devices
			Jean-Paul Noel
11/971566	US	01/09/2008	Light emitting devices with a zinc oxide thin film structure
			Brian Rioux

			Title of Patent and First Named
Patent or Application No.	Country	Filing Date	<u>Inventor</u>
PCT/CA2008/000020	WO	01/09/2008	Light emitting devices with a zinc oxide thin film structure
			Brian Rioux
PCT/CA2008/001607	WO	09/11/2008	Zinc oxide thin film
			electroluminescent devices
			Jean-Paul Noel
61/187424	US	06/16/2009	High Quality Gate Dielectric For
			Semiconductor Devices and Method fo Formation Thereof
			Carla Miner
PCT/CA2010/000287	WO	03/01/2010	Deposition of Thin Film
			Dielectrics and Light Emitting
			Nano-Layer Structures
			Jean-Paul Noel
60/610203	US	09/16/2004	Thin film alternating current
			solid-state lighting
			Steven E. Hill
11/229220	US	09/16/2005	Thin film alternating current
			solid-state lighting
			Steven E. Hill
PCT/CA2005/001418	WO	09/16/2005	Thin film alternating current
			solid-state lighting
			Steven E. Hill
61/083673	US	07/25/2008	Injectory Layer Structure for a light emitting device
			Unable to Verify
61/084427	US	07/29/2008	Tapered edge profile for use in
			light emitting structures
			Unable to Verify
61/084666	US	07/30/2008	Injector layer for electrodes of
			light emitting device
			Unable to Verify
61/085028	US	07/31/2008	Electroplate process for light
			emitting devices
			Unable to Verify
61/030349	US	02/21/2008	Visible emitters using rare earth
			doped oxide phosphors
			Unable to Verify
61/030687	US	02/22/2008	Electroluminescent devices with

Title of Patent and First Named

	Filing Date	<u>Inventor</u>
		vertical phosphors
		Unable to Verify
US	07/31/2008	Zinc oxide based light emitting
		devices fabricated using
		hydrogen plasma treatment
		TT 11 () TT 10
ric	07/02/2000	Unable to Verify
US	07/02/2009	Top side reflector
		Unable to Verify
US	07/16/2009	Electroplate process for light
		emitting devices
		Unable to Verify
US	07/09/2009	Injector layer structure for a light
		emitting device
7.10	A = /2 - /2 - /2 - /2 - /2 - /2 - /2 - /2	Unable to Verify
US	07/23/2009	Injector layer for electrode of
		light emitting device
		Unable to Verify
TP	12/22/2006	Pixel structure for a solid state
***	12/22/2000	light emitting device
		right chutting device
		George Chik
	US US US US JP	US 07/02/2009 US 07/16/2009 US 07/09/2009 US 07/23/2009

Assignor assigns to Assignee all rights to the inventions, invention disclosures, and discoveries in the assets listed above, together, with the rights, if any, to revive prosecution of claims under such assets and to sue or otherwise enforce any claims under such assets for past, present or future infringement.

Assignor hereby authorizes the respective patent office or governmental agency in each jurisdiction to make available to Assignee all records regarding the Certain Assets.

The terms and conditions of this Assignment of Rights in Certain Assets will inure to the benefit of Assignee, its successors, assigns, and other legal representatives and will be binding upon Assignor, its successors, assigns, and other legal representatives.

DATED this
$$\frac{21}{2}$$
 day of $\frac{\sqrt{3}}{\sqrt{3}}$ 2013.

ASSIGNOR:

RECORDED: 03/20/2013

Group IV Semiconductor, Inc.

By: S. NAOR

Title: C.E.O.